JC02 Recid PCT/PTO 06 JUNA

94326

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

n Re U.S. Pa	atent Application)	
pplicant:	√Takashi YOKOYAMA et al.)	I hereby certify that this correspondence is being deposited with the United Postal Service as first class mail in an envelope addressed to:
Serial No.:	10/534,946)	Mail Stop AMENDMENT, Commissioner of
· Filed:	May 11, 2005)	Patents, P.O. Box 1450, Alexandria, VA, 22313-1450, on June 1, 2005
For:	SILICON WAFER, ITS MANUFACTURING METHOD, AND ITS MANUFACTURING APPARATUS)	Gerald T. Shekleton Reg. No. 27,466

INFORMATION DISCLOSURE STATEMENT

Mail Stop AMENDMENT Commissioner for Patents P. O. Box 1450 Alexandria, VA 22313

Sir:

Pursuant to 37 C.F.R. §1.97, a list of documents is disclosed on the attached Form PTO-1449 that may be material to the examination of this application. The listed Documents are enclosed herewith.

No inferences should be drawn that the attached list represents a comprehensive investigation, or that any material disclosed is equivalent to the subject invention. In addition, none of the documents that have publication dates prior to the priority date of the above application anticipate the invention in this application.

No item of information contained in the information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application, and, to the knowledge of the person signing the certification after making reasonable inquiry, no item of information contained in the information disclosure statement was known to any individual designated in § 1.56(c) more than three months prior to the filing of the information disclosure statement.

The cited document(s) disclose numerous specific features. There has been no attempt to list each

Serial No.: 10/534,946

and every feature disclosed by each document. The Examiner is requested to review the document(s) and determine the extent of the materiality of the document disclosures with respect to the present invention.

The discussion of any art and the citation of any document(s) herein is not to be construed as an admission that the art or document disclosure is necessarily within the invention field of endeavor, that the art or document disclosure is necessarily prior in time to a particular date which may be relevant to the instant patent application, and/or that the art or document disclosure is otherwise necessarily prior art as defined by the patent law with respect to the instant invention and application.

Also, there is reserved the right to later set forth how the instant invention is distinguished over the disclosure of any document or other art, including the disclosures of the art and document(s) recited herein, that may be cited by the Examiner in rejecting a claim in the instant patent application. The recitation herein of the art and document(s) is not to be construed as an assertion that more pertinent art could not possibly be in existence.

Respectfully submitted,

WELSH & KATZ, LTD.

Ovald T. Shehles

Gerald T. Shekleton Registration No. 27,466

Dated: June 1, 2005 Welsh & Katz, Ltd.

120 South Riverside Plaza, 22nd Floor

Chicago, Illinois 60606 Telephone: 312/655-1500

PTO/SB/08A & (04-03)
Approved for use through 04/30/2003. OMB 0651-0031
U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT		Complete if Known		
		Application Number	10/534,946	
		Filing Date	May 11, 2005	
		First Named Inventor	YOKOYAMA et al.	
(use as many sheets as necessary)		Art Unit	Unassigned	
		Examiner Name	Unassigned	
Sheet	1	of 1	Attorney Docket Number	94326

	U.S. PATENT DOCUMENTS					
Examin er Initials*	Cite No.1	Document Number Number-Kind Code ^{2 (fl known)}	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear	
		with the state of				

		FOF	REIGN PATENT DO	CUMENTS		
Examiner Initials*	Cite No.1	Foreign Patent Document Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ₆
		JP 2001-278692	10/10/2001	Ryoji et al.		Abstract
		JP 2000-313695	11/14/2000	Toshio et al.		Abstract
		JP 2001-261495	09/26/2001	Kozo et al.		Abstract
		JP 8-330316	12/13/1996	Masataka et al.		Abstract
		JP 11-199387	07/27/1999	Hideki et al.		Abstract
		JP 11-79889	03/23/1999			No
		JP 2000-159594	06/13/2000	Kozo et al.	***************************************	Abstract
		JP 5345679	04/24/1978			No
		JP 54-119375	09/17/1979	Sadao et al.		Abstract
		JP 56-21758	02/28/1981	***************************************	······································	No
		JP 63-319288	12/27/1988	Hirotoshi		Abstract
		JP 2-172884	07/04/1990	Tomohiko et al.		Abstract
		JP 6-16490	01/25/1994		***************************************	No
		JP 6-56572	03/01/1994			No
		JP 5-319976	12/03/1993	Rintarou et al.		Abstract
**************************************		JP 7-89789	04/04/1995			No

NON PATENT LITERATURE DOCUMENTS				
Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T6		
	De Kock et al.; "The Effect of Doping on the Formation of Swirl defects in Dislocation-Free Czochralski-Grown Silicon Crystals," <i>Journal of Crystal Growth</i> , Vol. 49, 1980, pp. 718-734.			
		Cite No.¹ Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published. De Kock et al.; "The Effect of Doping on the Formation of Swirl defects in Dislocation-Free Czochralski-Grown Silicon Crystals," Journal of Crystal		

Examiner	Date	
Signature	Considered	

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Applicant's unique citation designation number (optional). ²See Kind Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁸Applicant is to place a check mark here if English language Translation is attached.

Burden Hour Statement: This form is estimated to take 2.0 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, Washington, DC 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Assistant Commissioner for Patents, Washington, DC 20231.